

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(semiconductor and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene)) and (metal adj interconnect\$4)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 09:57
L2	1	(semiconductor and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene)) and (metal adj interconnect\$4)).clm.	US-PGPUB	OR	ON	2006/11/21 09:57
L3	1026	(438/638).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/21 09:57
L4	10	semiconductor and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene)) and (metal adj interconnect\$4) and @ad<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 10:00
L18	857	(438/785).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/21 12:20
L19	53	semiconductor and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene)) and (interconnect\$4) and @ad<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:39

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S1	2469	((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 11:01
S2	222	substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:22
S3	112	((integrated adj circuit) or ("IC")) and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")).and (via or hole or opening or open or trench or (dual damascene))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:23
S4	55	((integrated adj circuit) or ("IC")) and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene)) and (interconnect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:26
S5	12	((integrated adj circuit) or ("IC")) and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene)) and (metal adj interconnect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/19 14:23
S6	8	((integrated adj circuit) or ("IC")) and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene)) and (metal adj interconnect\$4) and @ad<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/20 15:17

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S7	8	(("6,316,167") or ("6,573,030") or ("6,316,167") or ("6,309,955") or ("6,500,773") or ("6,117,619") or ("6,316,167") or ("6,620,727") or ("20030119307") or ("20040082173") or ("20050056940")).PN.	US-PGPUB; USPAT	OR	OFF	2006/07/20 11:17
S8	2679	(438/637).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/20 11:15
S9	984	(438/638).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/21 09:57
S10	418	(438/695).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/20 11:16
S11	791	(438/785).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/21 12:20
S12	196	(438/752).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/20 11:16
S14	2	(("20050104150") or ("20050167839")).PN.	US-PGPUB; USPAT	OR	OFF	2006/07/20 11:18
S15	1204	(438/753).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/20 14:50

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S16	10	semiconductor and substrate and ((dielectric or oxide or insulat\$4) adj (layer or film)) and ((tunable adj etch adj resistant adj (antireflective or anti-reflective)) or ("TERA")) and (via or hole or opening or open or trench or (dual damascene)) and (metal adj interconnect\$4) and @ad<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:37
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